

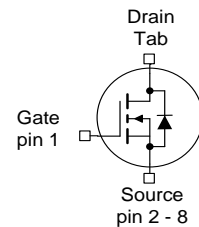
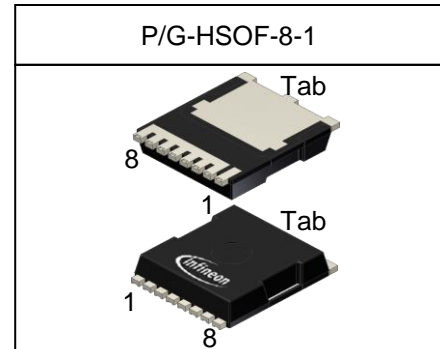
**OptiMOS™-5 Power-Transistor**

**Features**

- N-channel - Enhancement mode
- AEC-Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- Ultra low Rds(on)
- 100% Avalanche tested

**Product Summary**

$V_{DS}$	100	V
$R_{DS(on)}$	3.5	mΩ
$I_D$	150	A



Type	Package	Marking
IAUT150N10S5N035	P/G-HSOF-8-1	5N10035

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_C=25\text{ °C}, V_{GS}=10\text{V}$	150	A
		$T_C=100\text{ °C}, V_{GS}=10\text{ V}^{1)}$	95	
Pulsed drain current <sup>1)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$	600	
Avalanche energy, single pulse <sup>1)</sup>	$E_{AS}$	$I_D=75\text{ A}$	210	mJ
Avalanche current, single pulse	$I_{AS}$	-	120	A
Gate source voltage	$V_{GS}$	-	±20	V
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	166	W
Operating and storage temperature	$T_j, T_{stg}$	-	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	-	-	55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Thermal characteristics<sup>1)</sup></b>						
Thermal resistance, junction - case	$R_{thJC}$	-	-	-	0.9	K/W

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=110\text{ }\mu\text{A}$	2.2	3.0	3.8	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$	-	0.1	1	$\mu\text{A}$
		$V_{DS}=50\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=85\text{ °C}^{2)}$	-	1	20	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=6\text{ V}$ , $I_D=40\text{ A}$	-	3.7	5.0	$\text{m}\Omega$
		$V_{GS}=10\text{ V}$ , $I_D=75\text{ A}$	-	3.0	3.5	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics<sup>1)</sup>**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=50\text{ V},$ $f=1\text{ MHz}$	-	4700	6110	pF
Output capacitance	$C_{oss}$		-	780	1014	
Reverse transfer capacitance	$C_{rss}$		-	34	52	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50\text{ V}, V_{GS}=10\text{ V},$ $I_D=50\text{ A}, R_{G,ext}=3.5\ \Omega$	-	12	-	ns
Rise time	$t_r$		-	7	-	
Turn-off delay time	$t_{d(off)}$		-	23	-	
Fall time	$t_f$		-	26	-	

**Gate Charge Characteristics<sup>1)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=50\text{ V}, I_D=100\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	23	30	nC
Gate to drain charge	$Q_{gd}$		-	15	23	
Gate charge total	$Q_g$		-	67	87	
Gate plateau voltage	$V_{plateau}$		-	5.2	-	V

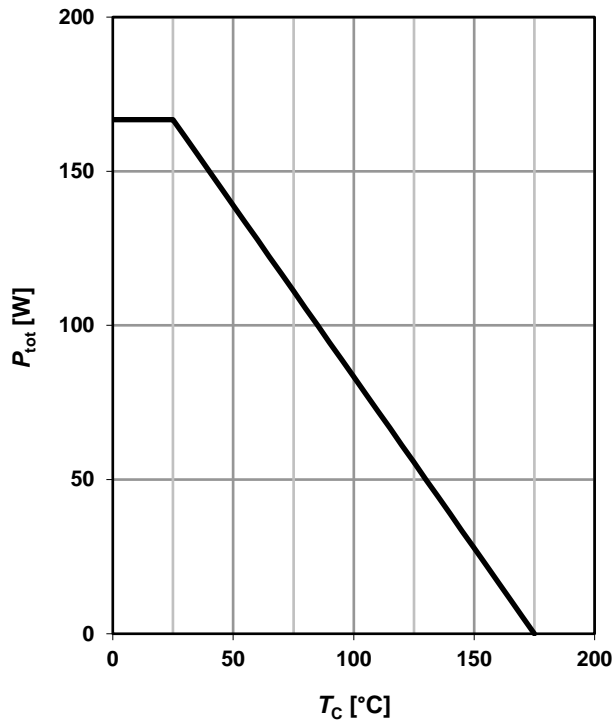
**Reverse Diode**

Diode continuous forward current <sup>1)</sup>	$I_S$	$T_C=25\text{ °C}$	-	-	150	A
Diode pulse current <sup>1)</sup>	$I_{S,pulse}$		-	-	600	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=75\text{ A},$ $T_j=25\text{ °C}$	-	0.9	1.3	V
Reverse recovery time <sup>1)</sup>	$t_{rr}$	$V_R=50\text{ V}, I_F=50\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	63	-	ns
Reverse recovery charge <sup>1)</sup>	$Q_{rr}$		-	120	-	nC

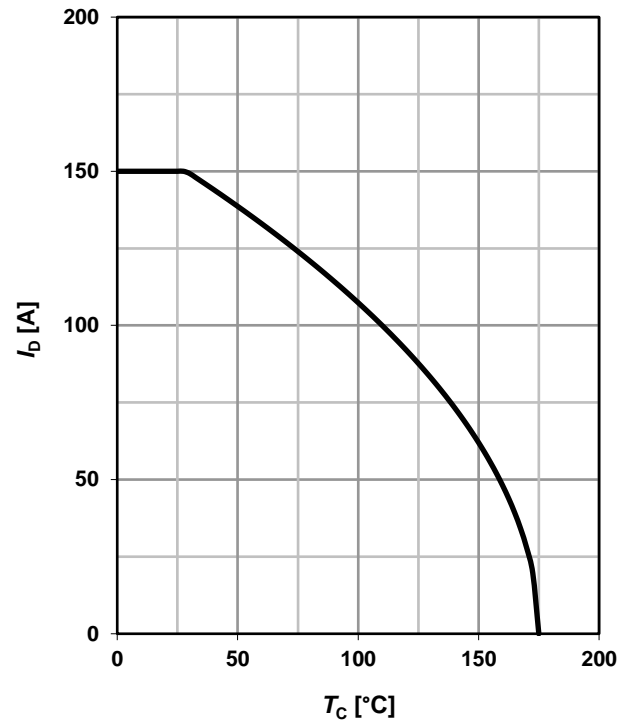
<sup>1)</sup> Defined by design. Not subject to production test.

**1 Power dissipation**

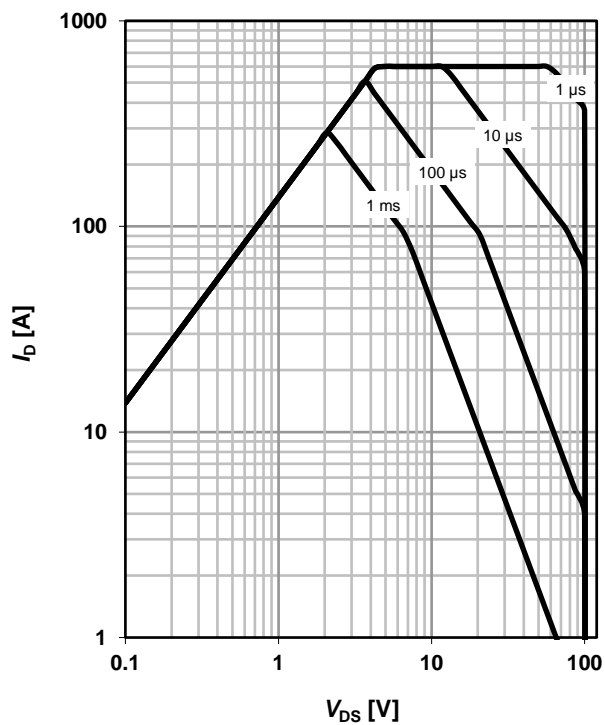
$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$


**2 Drain current**

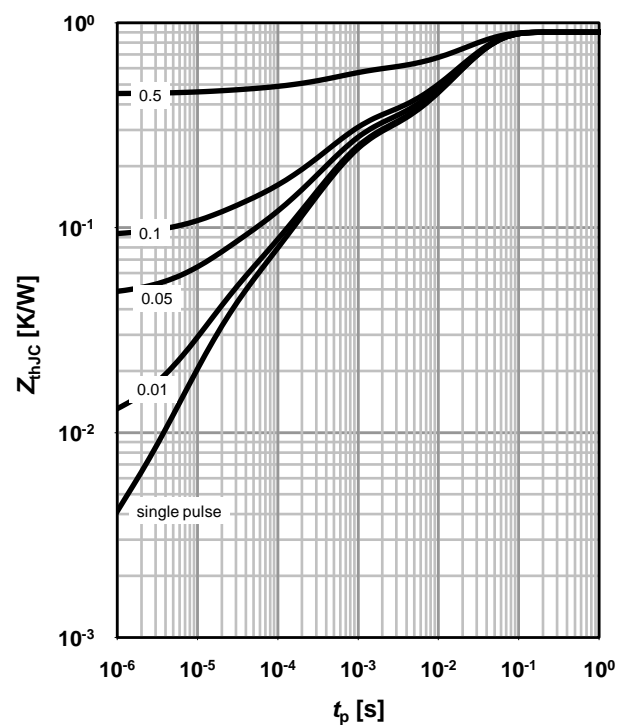
$$I_D = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$


**3 Safe operating area**

$$I_D = f(V_{\text{DS}}); T_C = 25^\circ\text{C}; D = 0$$

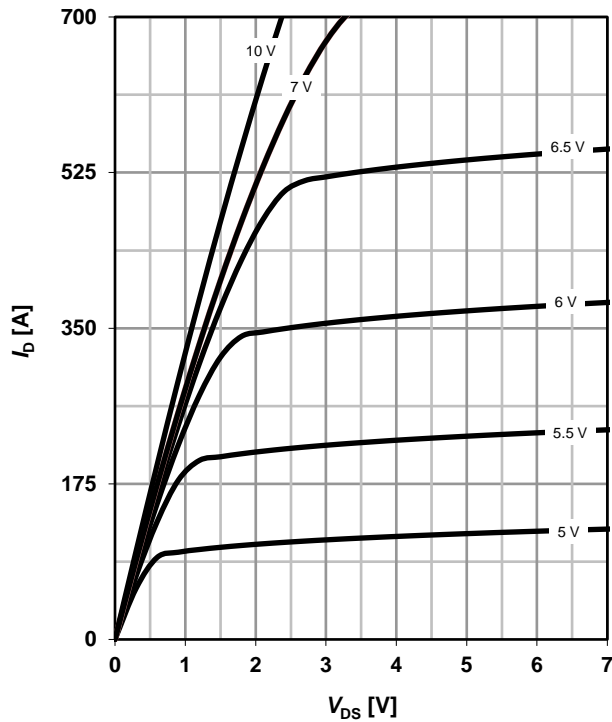
 parameter:  $t_p$ 

**4 Max. transient thermal impedance**

$$Z_{\text{thJC}} = f(t_p)$$

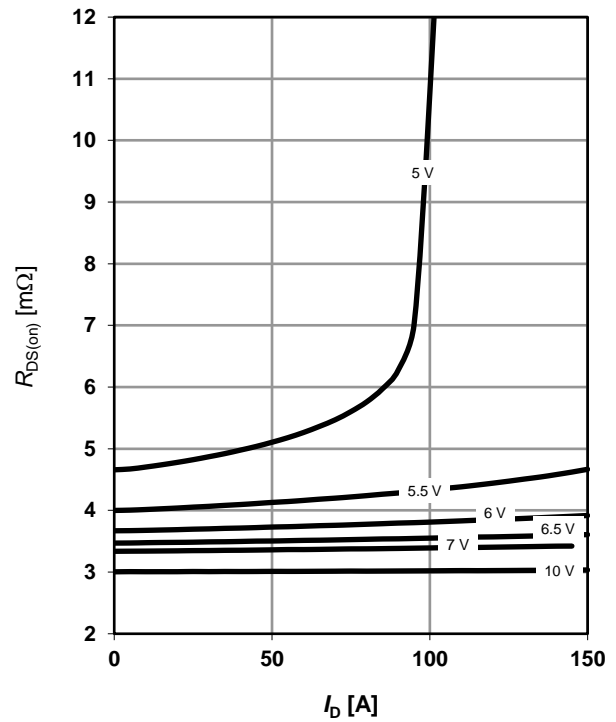
 parameter:  $D = t_p/T$ 


**5 Typ. output characteristics**

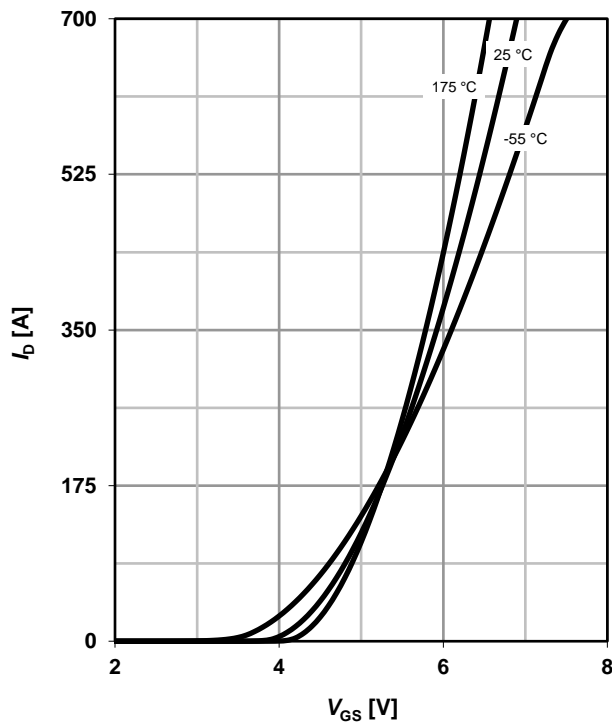
$$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$$

 parameter:  $V_{GS}$ 

**6 Typ. drain-source on-state resistance**

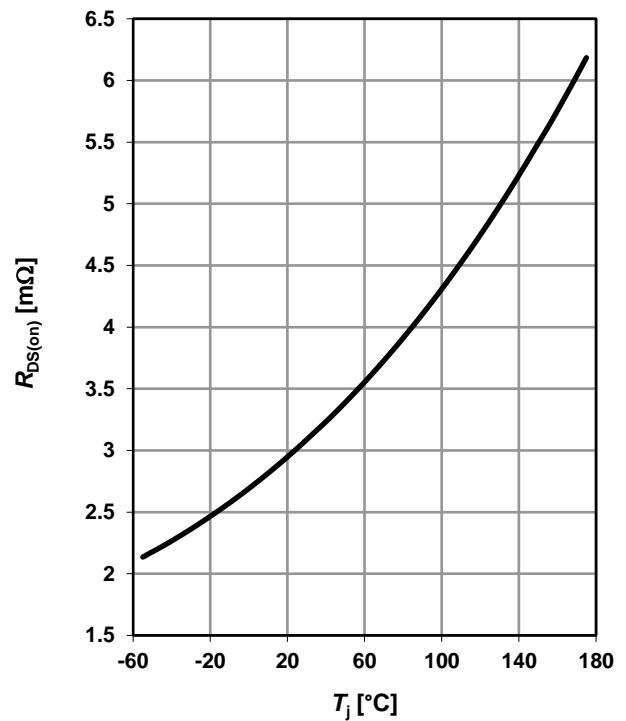
$$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$$

 parameter:  $V_{GS}$ 

**7 Typ. transfer characteristics**

$$I_D = f(V_{GS}); V_{DS} = 6\text{ V}$$

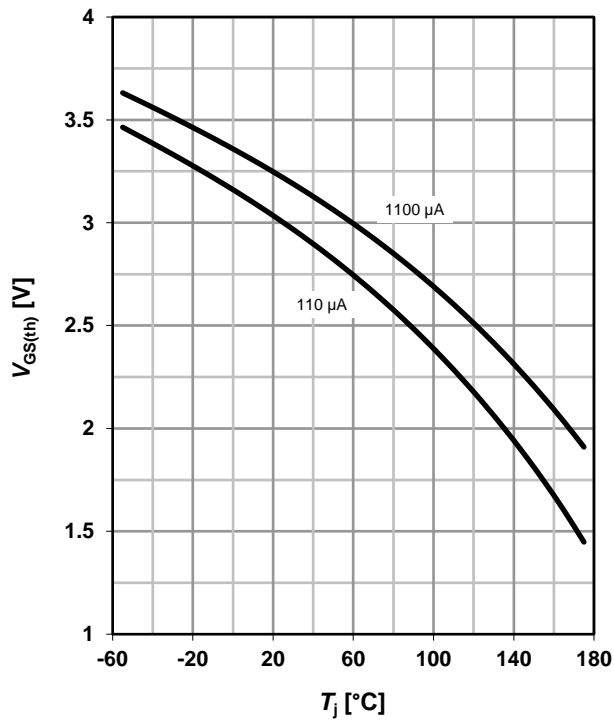
 parameter:  $T_j$ 

**8 Typ. drain-source on-state resistance**

$$R_{DS(on)} = f(T_j); I_D = 75\text{ A}; V_{GS} = 10\text{ V}$$

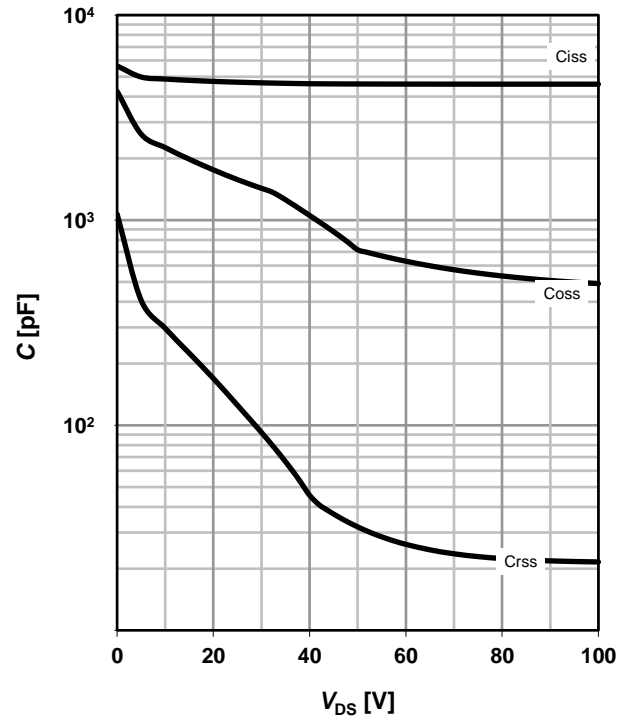


**9 Typ. gate threshold voltage**

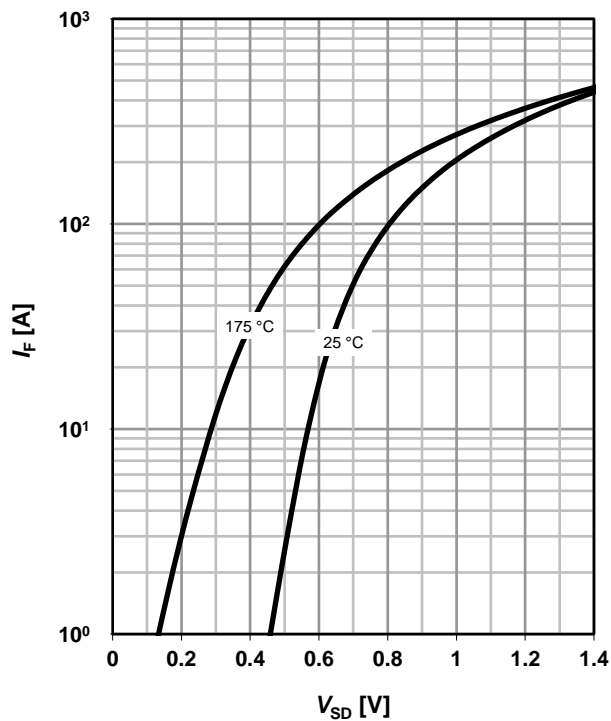
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

 parameter:  $I_D$ 

**10 Typ. capacitances**

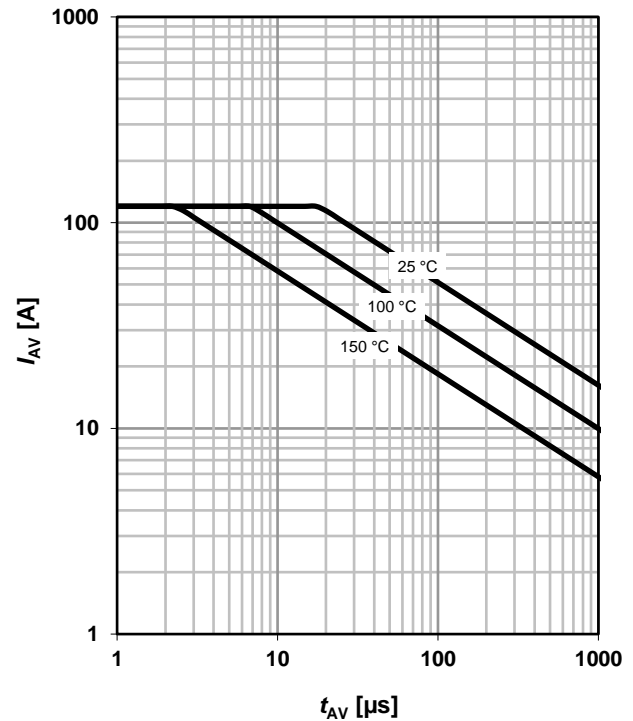
$$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$$


**11 Typical forward diode characteristics**

$$I_F = f(V_{SD})$$

 parameter:  $T_j$ 

**12 Typ. avalanche characteristics**

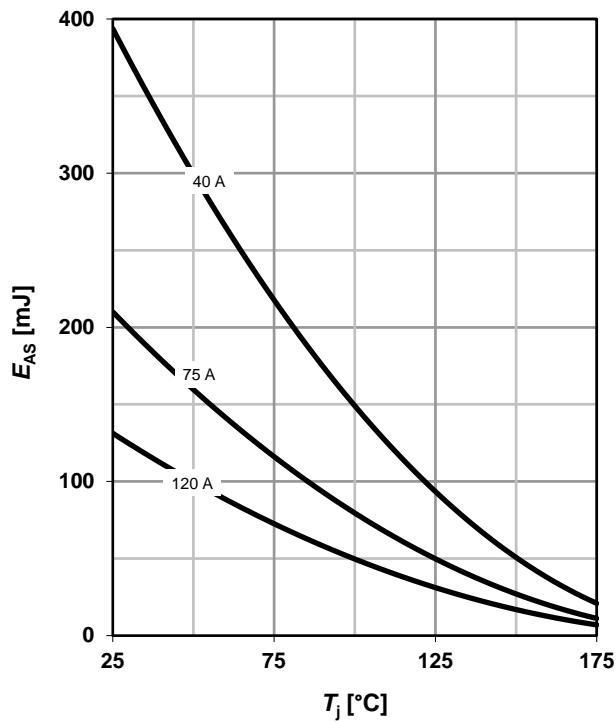
$$I_{AS} = f(t_{AV})$$

 parameter:  $T_{j(start)}$ 


### 13 Typical avalanche energy

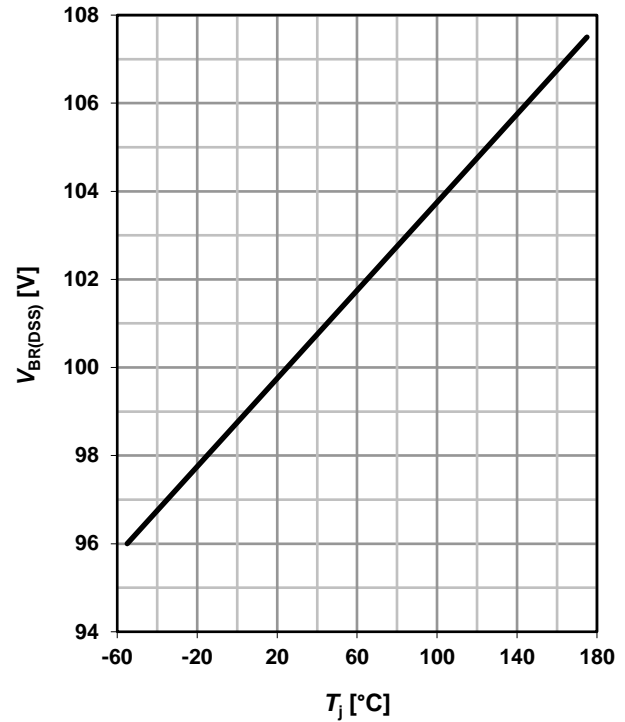
$$E_{AS} = f(T_j)$$

parameter:  $I_D$



### 14 Drain-source breakdown voltage

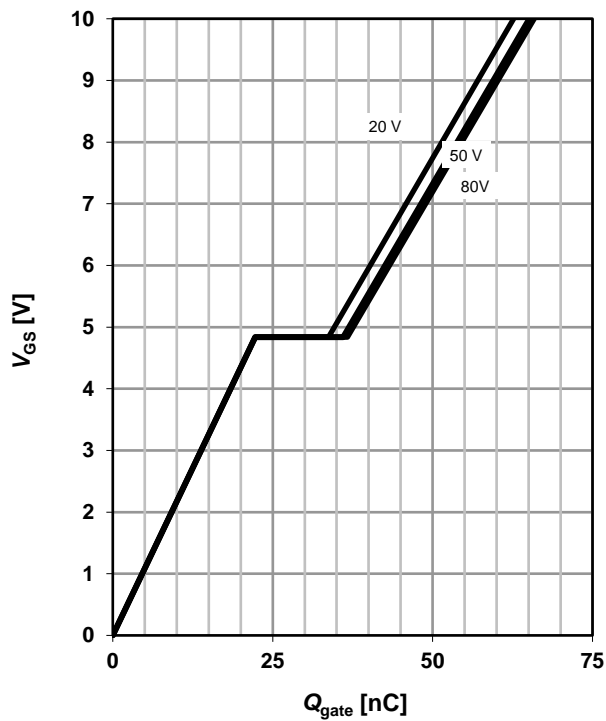
$$V_{BR(DSS)} = f(T_j); I_{D\_typ} = 1 \text{ mA}$$



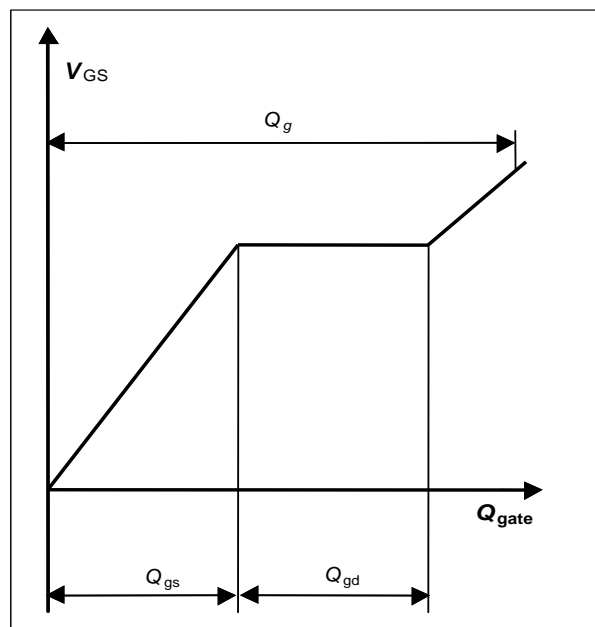
### 15 Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = 100 \text{ A pulsed}$$

parameter:  $V_{DD}$



### 16 Gate charge waveforms



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## Revision History

Version	Date	Changes
Version 1.0	02.10.2017	Final Data Sheet
Version 2.0	14.03.2019	Updated avalanche parameters